ABSTRACT OF THE DISCLOSURE

In the processing method of the present invention, there is implemented irradiation with a charged particle beam in such a manner that, when executing processing in a uniform manner, when deposition processing or etching processing of a prescribed pattern is carried out using a charged particle beam apparatus, a region of the pattern to be processed is divided up into microscopic regions corresponding to the diameter of the beam, and regulation is performed by scanning circuits etc. with processing proceeding simultaneously for a plurality of patterns within the scanning region in such a manner that the dose amount for each microscopic region becomes equal.